

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead-free

DESCRIPTION

SBESDL03C-C is a low-capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With typical capacitance of 0.25pF, it is designed to protect parasitic sensitive systems against over voltage and over current transient events. It complies with IEC 61000-4-2 (ESD) Level 4, IEC 61000-4-4 (EFT), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

It uses ultra-small DFN1006 package. Each device can protect one high-speed data line. It offers system designers flexibility to protect single data line where space is a premium concern. The combined features of low capacitance, ultra-small size and high ESD robustness make SBESDL03C-C ideal for high-speed data port and high-frequency line applications, such as cellular phones and HD visual devices.

FEATURES

- Transient Protection for High-Speed Data Lines
- IEC61000-4-2 Level 4 ESD Protection
- Low Capacitance and Clamping Voltage
- Low Leakage Current
- Flammability Rating: UL 94V-0

MARKING

3BU

PACKAGE INFORMATION

Package	MPQ	Leader Size
DFN1006	10K	7 inch

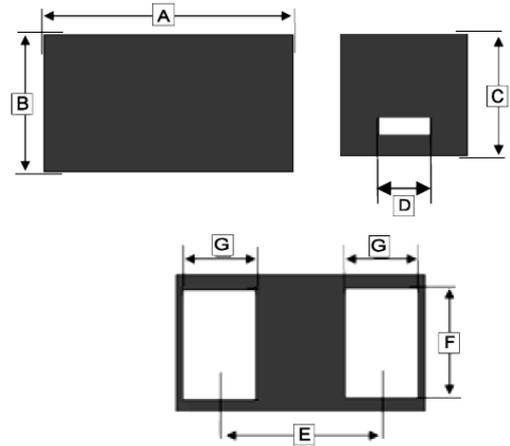
ORDER INFORMATION

Part Number	Type
SBESDL03C-C	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted.)

Parameter		Symbol	Ratings	Unit
IEC 61000-4-2 ESD Voltage	Air	V _{ESD}	±20	kV
	Contact		±20	
Peak Pulse Power		P _{PP}	100	W
Peak Pulse Current		I _{PP}	4	A
Maximum Lead Solder Temperature (10 Second Duration)		T _L	260	°C
Operating Junction Temperature Range		T _J	-55~125	
Storage Temperature Range		T _{STG}	-55~150	

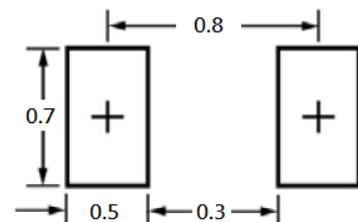
DFN1006



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.95	1.075	E	0.64 BSC.	
B	0.55	0.675	F	0.45	0.55
C	0.40	0.55	G	0.20	0.30
D	0.20 TYP.				



Mounting Pad Layout



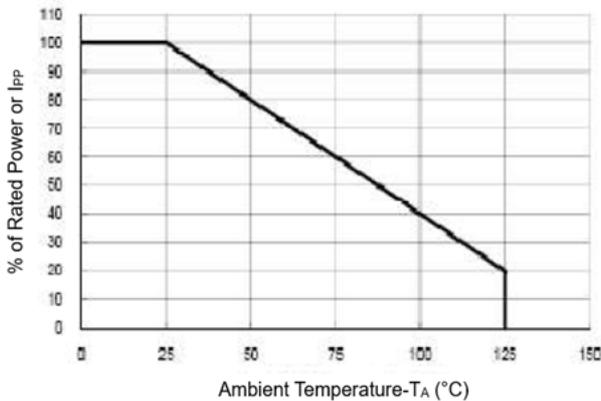
*Dimensions in millimeters

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted.)

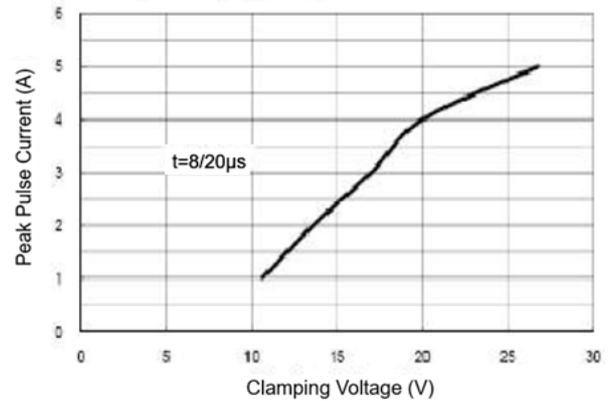
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Stand-off Voltage	V_{RWM}	-	-	3.3	V	
Breakdown Voltage	$V_{(BR)}$	4.2	-	-	V	$I_T=1\text{mA}$
Clamping Voltage @ $t_p=8/20\mu\text{s}$	V_C	-	-	12	V	$I_{PP}=1\text{A}$
		-	-	25		$I_{PP}=4\text{A}$
Reverse Leakage Current	I_R	-	-	100	nA	$V_{RWM}=3.3\text{V}$
Junction Capacitance	C_J	-	0.25	-	pF	$V_R=0\text{V}$, $f=1\text{MHz}$

TYPICAL CHARACTERISTICS

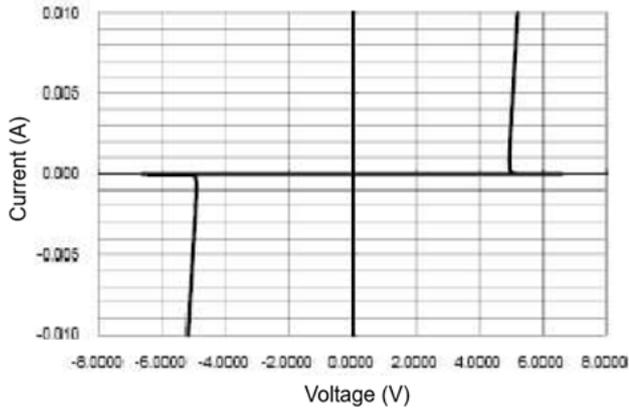
Power Derating Curve



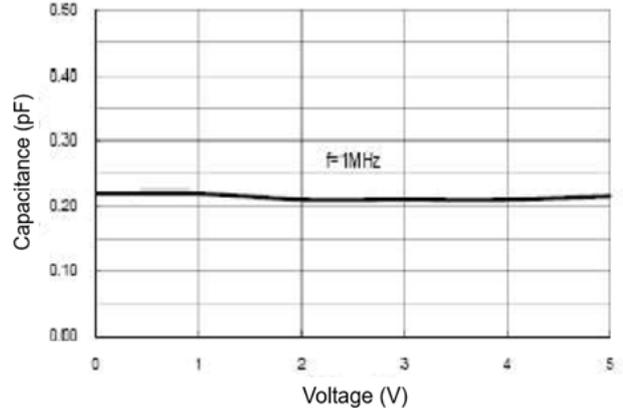
Clamping Voltage v.s Peak Pulse Current



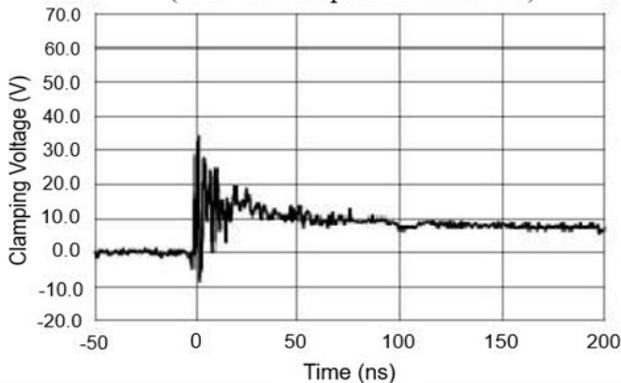
Voltage Sweeping



Voltage v.s Capacitance



ESD Clamping
(+8kV Contact per IEC 61000-4-2)



ESD Clamping
(-8kV Contact per IEC 61000-4-2)

